

NDF04N60Z, NDD04N60Z

N-Channel Power MOSFET 600 V, 2.0 Ω

Features

- Low ON Resistance
- Low Gate Charge
- ESD Diode-Protected Gate
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	NDF	NDD	Unit
Drain-to-Source Voltage	V_{DSS}	600		V
Continuous Drain Current $R_{\theta,JC}$ (Note 1)	I_D	4.8	4.1	A
Continuous Drain Current $R_{\theta,JC}$, $T_A = 100^\circ\text{C}$ (Note 1)	I_D	3.0	2.6	A
Pulsed Drain Current, $V_{GS} @ 10\text{V}$	I_{DM}	20	20	A
Power Dissipation $R_{\theta,JC}$	P_D	30	83	W
Gate-to-Source Voltage	V_{GS}	± 30		V
Single Pulse Avalanche Energy, $I_D = 4.0$ A	E_{AS}	120		mJ
ESD (HBM) (JESD22-A114)	V_{esd}	3000		V
RMS Isolation Voltage ($t = 0.3$ sec., R.H. $\leq 30\%$, $T_A = 25^\circ\text{C}$) (Figure 15)	V_{ISO}	4500	-	V
Peak Diode Recovery (Note 2)	dV/dt	4.5		V/ns
MOSFET dV/dt	dV/dt	60		V/ns
Continuous Source Current (Body Diode)	I_S	4.0		A
Maximum Temperature for Soldering Leads	T_L	260		$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

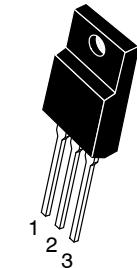
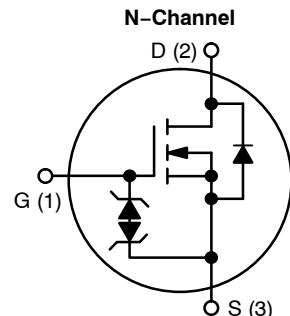
1. Limited by maximum junction temperature
2. $I_{SD} = 4.0$ A, $di/dt \leq 100$ A/ μs , $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$



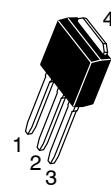
ON Semiconductor®

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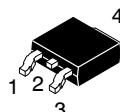
V_{DSS} (@ T_{Jmax})	$R_{DS(on)}$ (MAX) @ 2 A
650 V	2.0 Ω



NDF04N60ZG,
NDF04N60ZH
TO-220FP
CASE 221AH



NDD04N60Z-1G
IPAK
CASE 369D



NDD04N60ZT4G
DPAK
CASE 369AA

ORDERING AND MARKING INFORMATION

See detailed ordering, marking and shipping information on page 6 of this data sheet.

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THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) NDF04N60Z NDD04N60Z	$R_{\theta JC}$	4.2 1.5	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient Steady State (Note 3) NDF04N60Z (Note 4) NDD04N60Z (Note 3) NDD04N60Z-1	$R_{\theta JA}$	50 38 80	
3. Insertion mounted 4. Surface mounted on FR4 board using 1" sq. pad size (Cu area = 1.127 in sq [2 oz] including traces).			

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	BV_{DSS}	600			V
Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 1 \text{ mA}$	$\Delta BV_{DSS}/\Delta T_J$		0.6		$^{\circ}\text{C}/\text{V}$
Drain-to-Source Leakage Current	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0 \text{ V}$	25°C	I_{DSS}		1	μA
		150°C			50	
Gate-to-Source Forward Leakage	$V_{GS} = \pm 20 \text{ V}$	I_{GSS}			± 10	μA

ON CHARACTERISTICS (Note 5)

Static Drain-to-Source On-Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 2.0 \text{ A}$	$R_{DS(on)}$		1.8	2.0	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 50 \mu\text{A}$	$V_{GS(th)}$	3.0	3.9	4.5	V
Forward Transconductance	$V_{DS} = 15 \text{ V}$, $I_D = 2.0 \text{ A}$	g_{FS}		3.3		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 6)	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$	C_{iss}	427	535	640	pF
Output Capacitance (Note 6)		C_{oss}	50	62	75	
Reverse Transfer Capacitance (Note 6)		C_{rss}	8	14	20	
Total Gate Charge (Note 6)	$V_{DD} = 300 \text{ V}$, $I_D = 4.0 \text{ A}$, $V_{GS} = 10 \text{ V}$	Q_g	10	19	29	nC
Gate-to-Source Charge (Note 6)		Q_{gs}	2	3.9	6	
Gate-to-Drain ("Miller") Charge		Q_{gd}	5	10	15	nC
Plateau Voltage		V_{GP}		6.5		V
Gate Resistance		R_g		4.7		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	$V_{DD} = 300 \text{ V}$, $I_D = 4.0 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_G = 5 \Omega$	$t_{d(on)}$		13		ns
Rise Time		t_r		9.0		
Turn-Off Delay Time		$t_{d(off)}$		24		
Fall Time		t_f		15		

SOURCE-DRAIN DIODE CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Diode Forward Voltage	$I_S = 4.0 \text{ A}$, $V_{GS} = 0 \text{ V}$	V_{SD}			1.6	V
Reverse Recovery Time	$V_{GS} = 0 \text{ V}$, $V_{DD} = 30 \text{ V}$	t_{rr}		285		μC
Reverse Recovery Charge		Q_{rr}		1.3		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Width $\leq 380 \mu\text{s}$, Duty Cycle $\leq 2\%$.
6. Guaranteed by design.

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TYPICAL CHARACTERISTICS

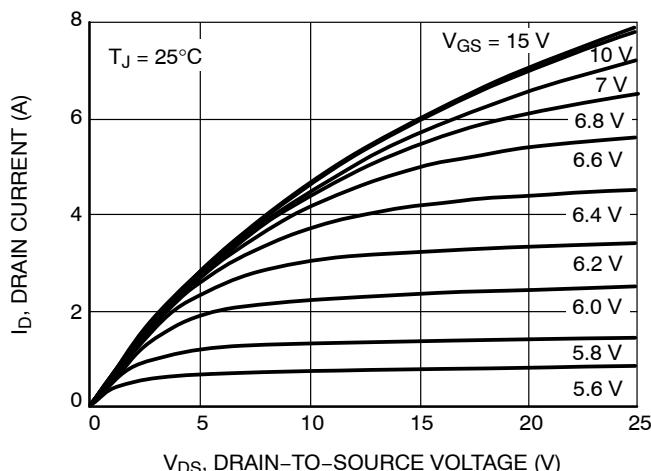


Figure 1. On-Region Characteristics

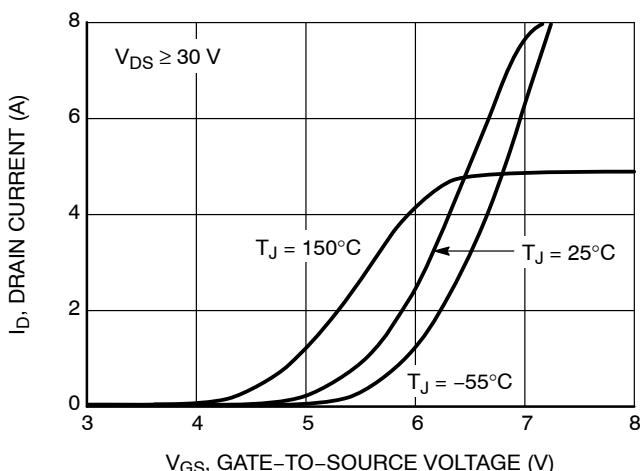


Figure 2. Transfer Characteristics

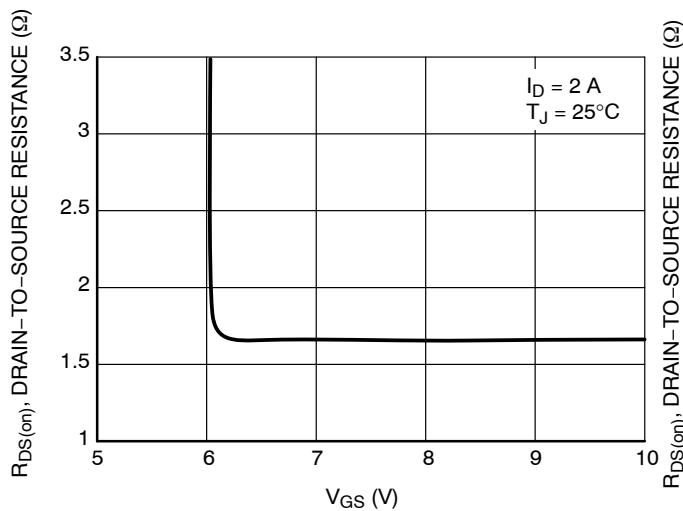


Figure 3. On-Resistance vs. Gate Voltage

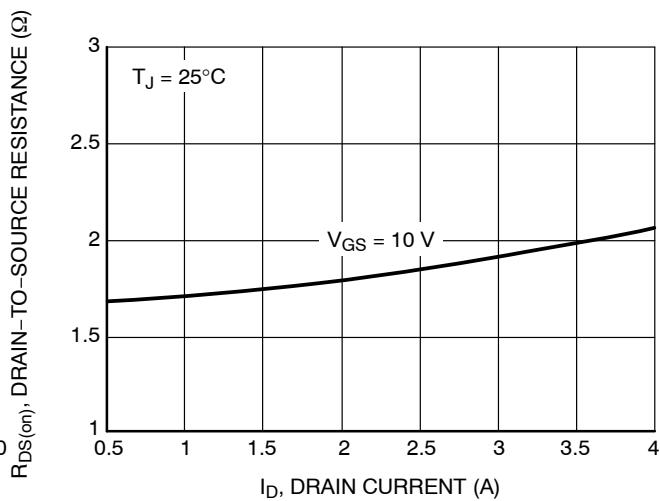


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

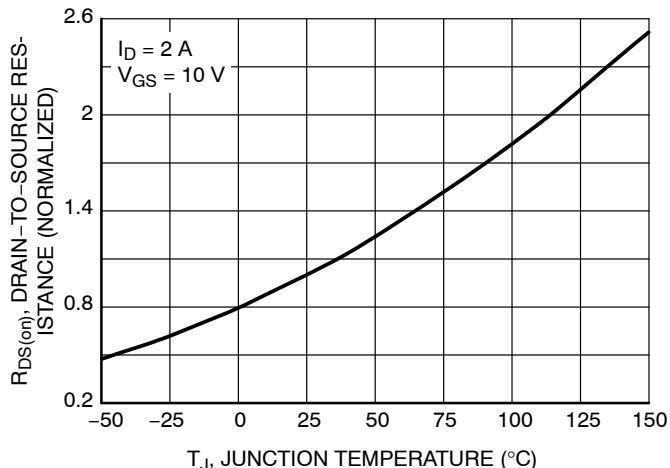


Figure 5. On-Resistance Variation with Temperature

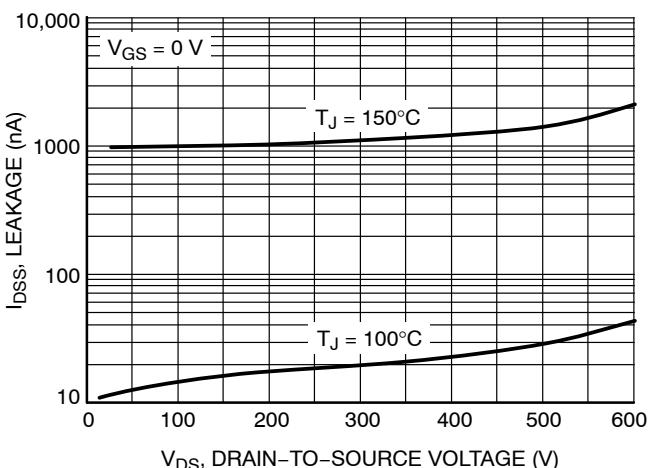


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

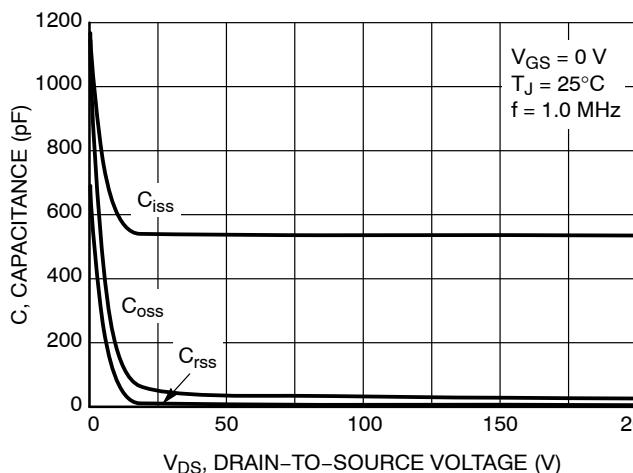


Figure 7. Capacitance Variation

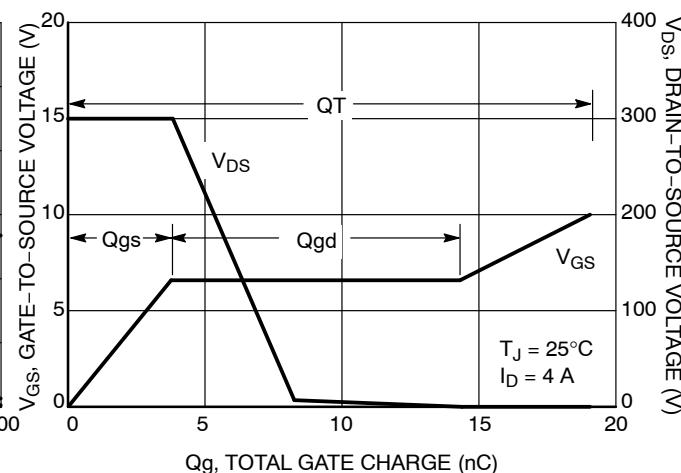


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

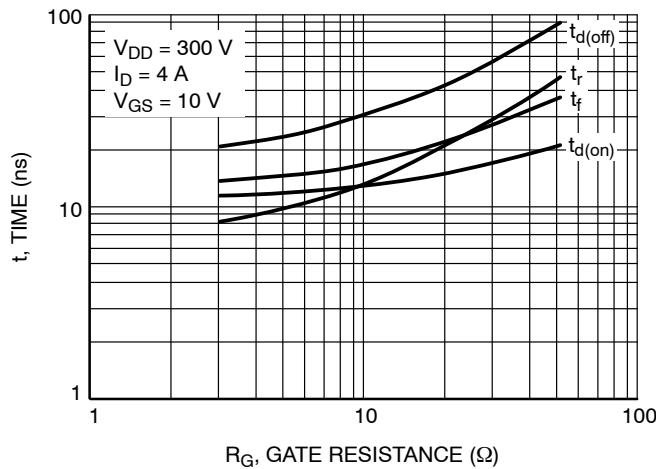


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

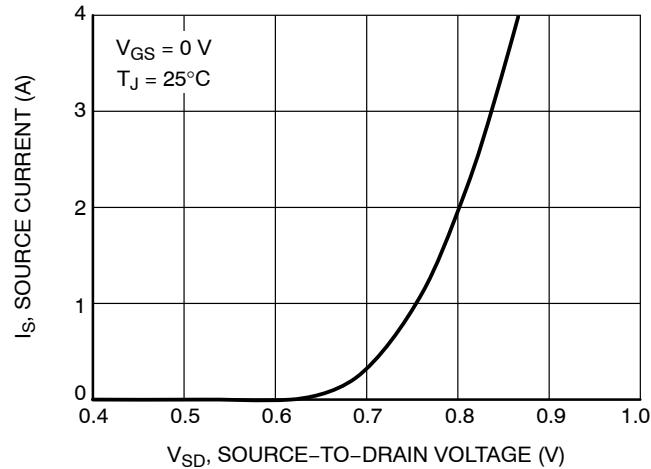


Figure 10. Diode Forward Voltage vs. Current

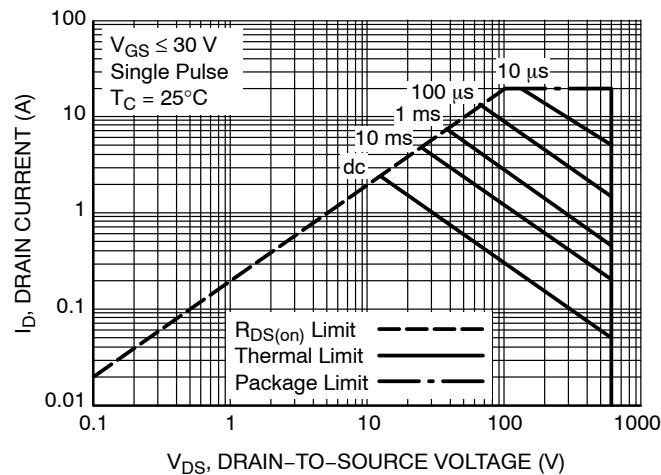


Figure 11. Maximum Rated Forward Biased Safe Operating Area for NDF04N60Z

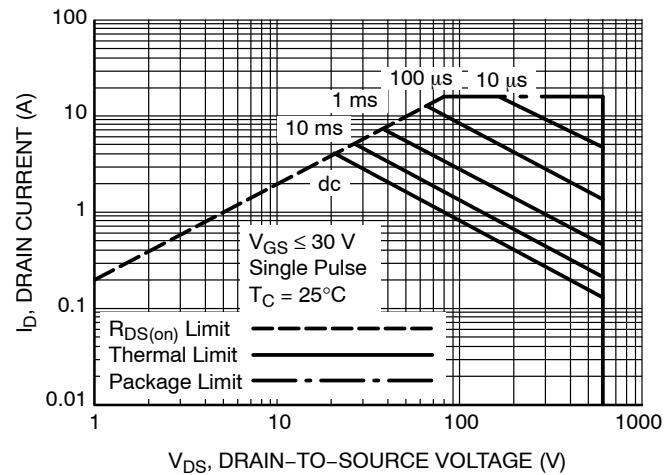


Figure 12. Maximum Rated Forward Biased Safe Operating Area for NDD04N60Z

NDF04N60Z, NDD04N60Z

TYPICAL CHARACTERISTICS

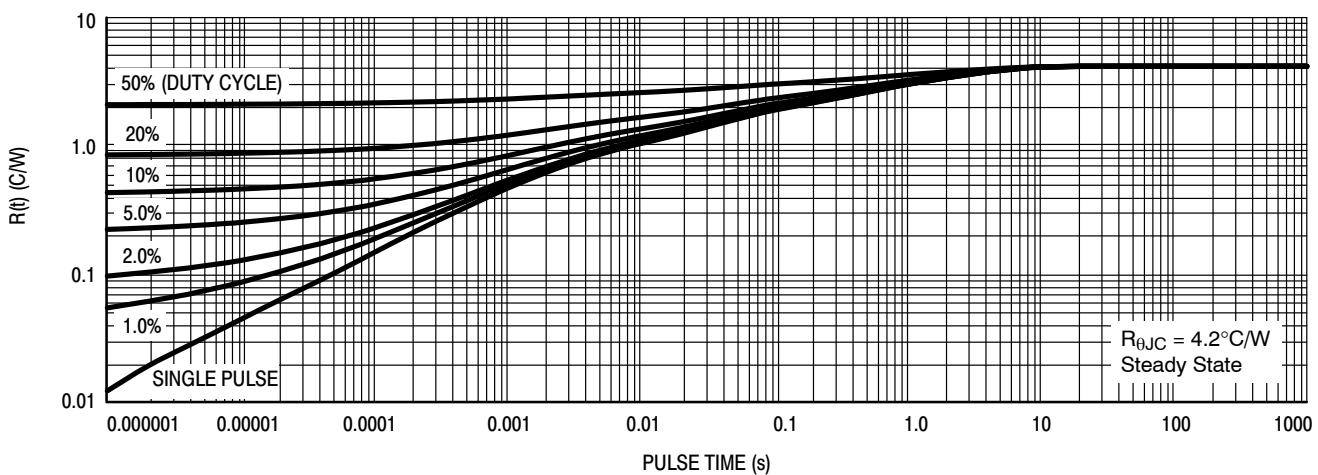


Figure 13. Thermal Impedance for NDF04N60Z

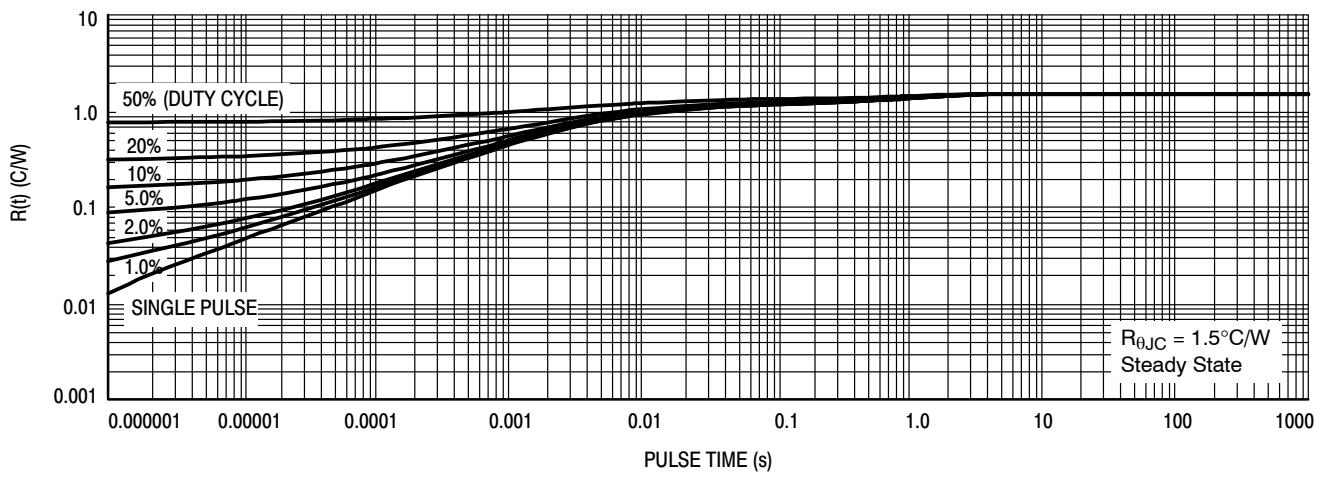


Figure 14. Thermal Impedance for NDD04N60Z

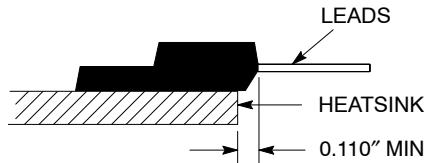


Figure 15. Mounting Position for Isolation Test

Measurement made between leads and heatsink with all leads shorted together.

*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

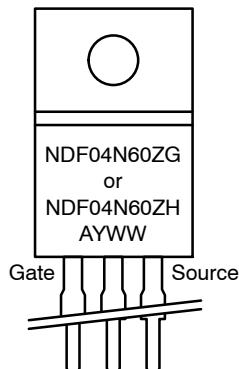
NDF04N60Z, NDD04N60Z

ORDERING INFORMATION

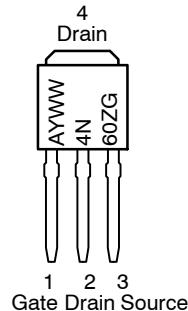
Order Number	Package	Shipping [†]
NDF04N60ZG	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail
NDF04N60ZH	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail
NDD04N60Z-1G	IPAK (Pb-Free, Halogen-Free)	75 Units / Rail
NDD04N60ZT4G	DPAK (Pb-Free, Halogen-Free)	2500 / Tape and Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

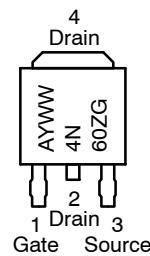
MARKING DIAGRAMS



TO-220FP



IPAK



DPAK

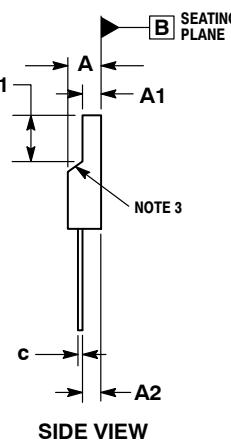
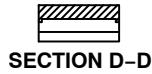
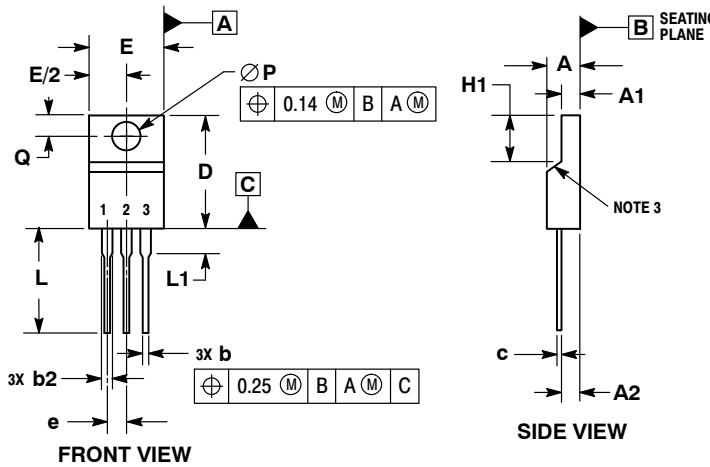
A = Location Code*
 Y = Year
 WW = Work Week
 G, H = Pb-Free, Halogen-Free Package

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

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PACKAGE DIMENSIONS

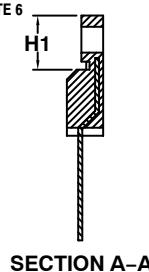
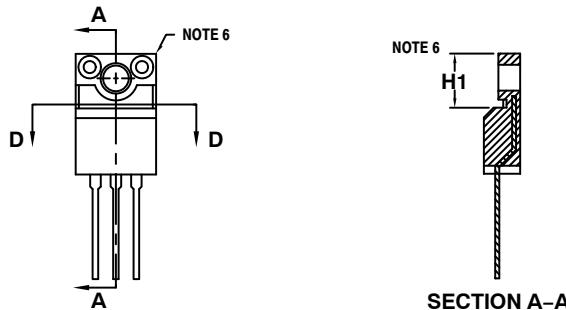
TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

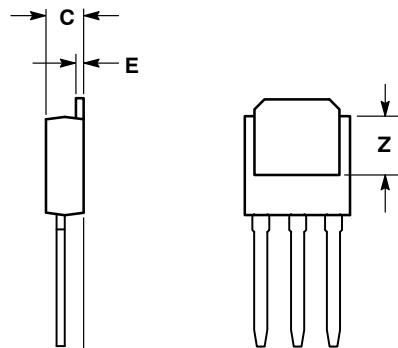
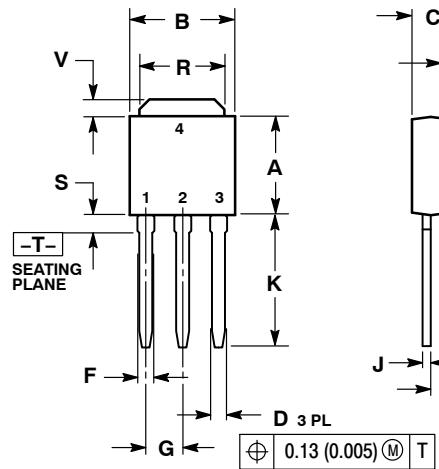
DIM	MILLIMETERS	
	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20



NDF04N60Z, NDD04N60Z

PACKAGE DIMENSIONS

IPAK CASE 369D ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER
ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

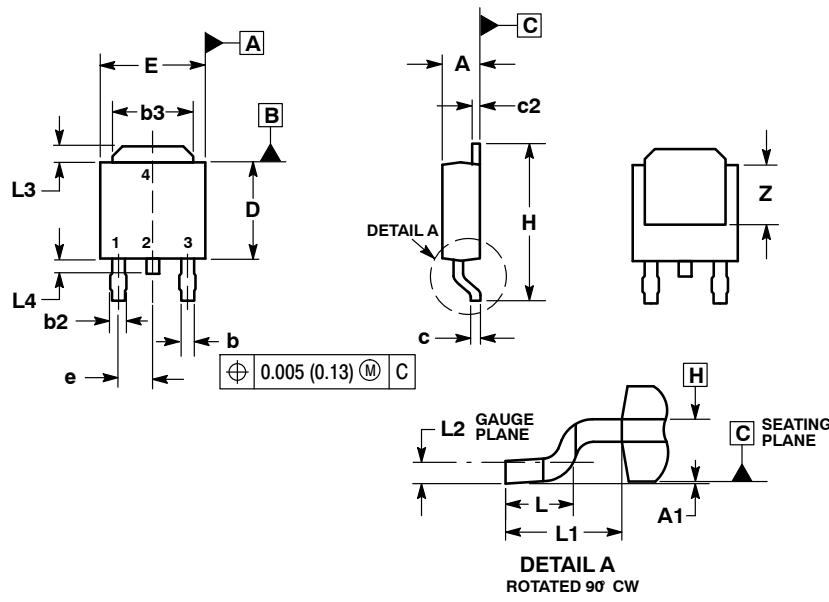
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	----	3.93	----

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NDF04N60Z, NDD04N60Z

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369AA ISSUE B



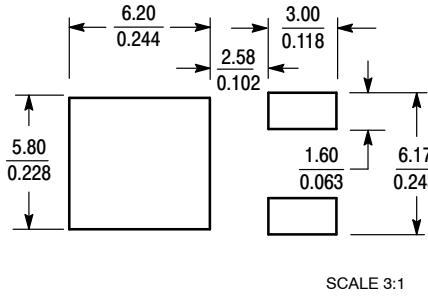
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm
inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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